MSKSEMI 美森科













ESD

1/5

TSS

MOV

GDT

PIFD

MSESD0511T

Product specification





Features

Capacitance: 3.5pF(typ.)
Reverse Working Voltage: 5V
IEC 61000-4-2 (ESD Air): ±25KV
IEC 61000-4-2 (ESD Contact): ±20KV

IEC 61000-4-5 (Lightning 8/20µs): 2.5A

Applications

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

Reference News

DFN1006	Schematic Diagram	Marking
		AN

Limiting Values(T_A = 25 °C, unless otherwise specified)

Symbol	Parameter	Conditions	Min	Max	Unit
Vesd	Electrostatic Discharge Voltage	IEC 61000-4-2; Contact Discharge	-	±20	kV
		IEC 61000-4-2; Air Discharge	-	±25	kV
P _{PP}	Peak Pulse Power	t _P = 8/20 µs	-	40	W
Іррм	Rated Peak Pulse Current	t _P = 8/20 µs	-	2.5	Α
ТА	Ambient Temperature Range	-	-55	150	°C
Tstg	Storage Temperature Range	-	-55	150	°C

Electrical Characteristics(T_A = 25 °C unless otherwise specified)

Symbol	Parameter	Conditions	Min	Тур.	Max	Unit
VRWM	Reverse Working Voltage	T _A = 25 °C	-	-	5.0	V
VBR	Breakdown Voltage	I _R = 1mA; T _A = 25 °C	5.6	-	9.0	V
I R	Reverse Leakage Current	V _{RWM} = 5V; T _A = 25 °C	-	-	100	nA
Vc	Clamping Voltage	I _{PP} = 1A, t _P =8/20µs	-	-	13	V
		I _{PP} =2.5A, t _P =8/20μs	-	-	16	V
Сл	Junction Capacitance	V _R = 0V, f = 1 MHz	-	3.5	4.0	pF



Typical Characteristics

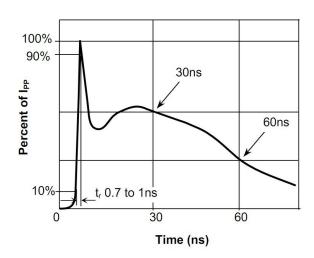


Fig.1 Pulse Waveform-ESD (IEC61000-4-2)

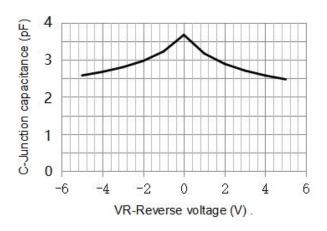


Fig.3 Capacitance vs. Reveres Voltage

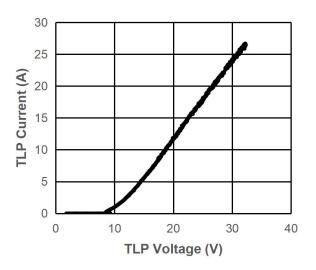


Fig.2 Transmission Line Pulse (TLP)

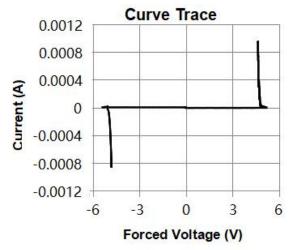
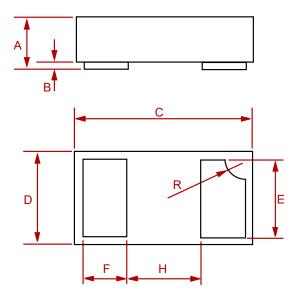


Fig.4 IV Curve (Forward Voltage)

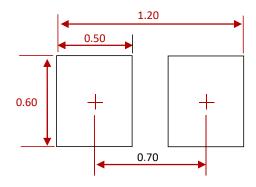


PACKAGEMECHANICALDATA



D :	Inches		Millimeters		
Dim	MIN	MAX	MIN	MAX	
А	0.0125	0.02	0.32	0.52	
В	0.000	0.002	0.00	0.05	
С	0.037	0.043	0.95	1.080	
D	0.022	0.027	0.55	0.680	
E	0.016	0.024	0.40	0.60	
F	0.008	0.012	0.20	0.30	
Н	0.015Typ.		0.40	Тур.	
R	0.001	0.005	0.05	0.15	

Suggested Pad Layout



NOTES:

- ${\bf 1.} \quad {\bf CONTROLLING\ DIMENSIONS\ ARE\ IN\ MILLIMETERS\ (ANGLES\ IN\ DEGREES)}.$
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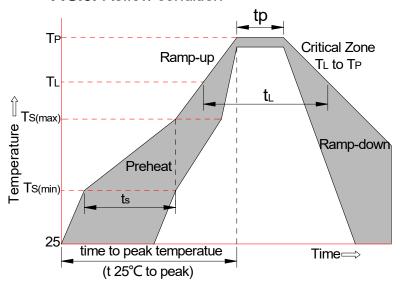
Order information

Orderable Device	Package	Packing Option
MSESD0511T	DFN1006	10000PCS



SolderingParameters

FIG.5: Reflow condition



Reflow Condition		Pb-Free Assembly		
	-Temperature Min (T _{s(min)})	+150°C		
Pre-heat	-Temperature Max(T _{s(max)})	+200°C		
	-Time (Min to Max) (ts)	60-180 secs.		
Average ramp up rate (Liquid us Temp (T _L) to peak)		3°C/sec. Max		
T _{s(max)} to T _L - Ramp-up Rate		3°C/sec. Max		
Reflow	-Temperature(T∟)(Liquid us)	+217°C		
	-Temperature(t∟)	60-150 secs.		
Peak Temp (T _p)		+260(+0/-5)°C		
Time within 5°C of actual Peak Temp (t _p)		30 secs. Max		
Ramp-down Rate		6°C/sec. Max		
xTime 25°C to Peak Temp (T _P)		8 min. Max		
Do not exceed		+260°C		



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